

Features

- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

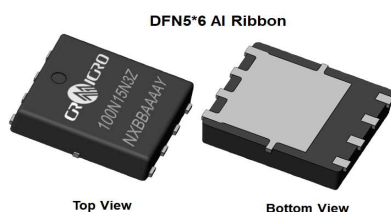
Applications

- Synchronous Rectification for AC/DC Quick Charger
- Battery management
- UPS (Uninterruptible Power Supplies)

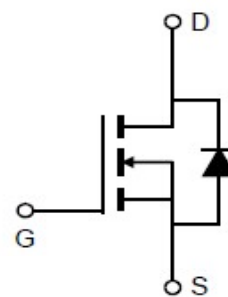
Product Summary

V_{DS}	150V
$R_{DS(on)}@10V_{typ}$	9.5mΩ
I_D	75A

100% Avalanche Tested
100% DVDS Tested



CRSM100N15N3Z



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSM100N15N3Z	100N15N3Z	DFN5*6 Rib	Tape&Reel	N/A	N/A	5000/4000p CS

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	150	V
Continuous drain current	I_D	75	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		52	
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D \text{ pulse}}$	300	A
Avalanche energy, single pulse ($I_{AS}=30A$, $R_g=25\Omega$)	E_{AS}	225	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	128	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	0.75	1.0	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	60.5	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	150	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.1	1	μA	$V_{DS}=120V, V_{GS}=0V$ $T_j=25^\circ C$
		-	10	100		$T_j=125^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	9.5	10.8	mΩ	$V_{GS}=10V, I_D=40A$
		-	10.5	12.1		$V_{GS}=8V, I_D=20A$
Transconductance	g_{fs}	-	55	-	S	$V_{DS}=5V, I_D=40A$

Dynamic Characteristic

Input Capacitance	C_{iss}	1470.7	2206	3309	pF	$V_{GS}=0V, V_{DS}=75V,$ $f=1MHz$
Output Capacitance	C_{oss}	254.2	381.3	571.95		
Reverse Transfer Capacitance	C_{rss}	20	30	60		
Gate Total Charge	Q_G	22.7	34	51.0	nC	$V_{GS}=10V, V_{DS}=75V,$ $I_D=40A, f=1MHz$
Gate-Source charge	Q_{gs}	9.9	14.9	22.4		
Gate-Drain charge	Q_{gd}	4.8	7.2	10.8		
Turn-on delay time	$t_{d(on)}$	7.3	14.6	29.2	ns	$V_{GS}=10V,$ $V_{DD}=75V,$ $I_D=44A, R_{G_ext}=2.7\Omega$
Rise time	t_r	40.3	80.6	161.2		
Turn-off delay time	$t_{d(off)}$	11.15	22.3	44.6		
Fall time	t_f	29.35	58.7	117.4		

Gate resistance	R_G	1	1.45	2.2	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$
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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.7	1.00	1.30	V	$V_{GS}=0V, I_{SD}=40A$
Body Diode Continuous Forward Current	I_S	-	-	75	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	300	A	TC = 25°C
Body Diode Reverse Recovery Time	t_{rr}	49.26	73.89	110.835	ns	$I_F=40A, dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	114.67	172	258	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

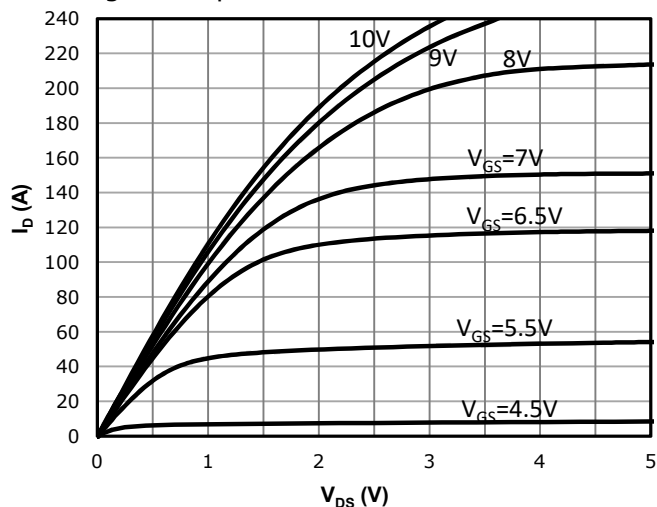


Fig 2: Transfer Characteristics

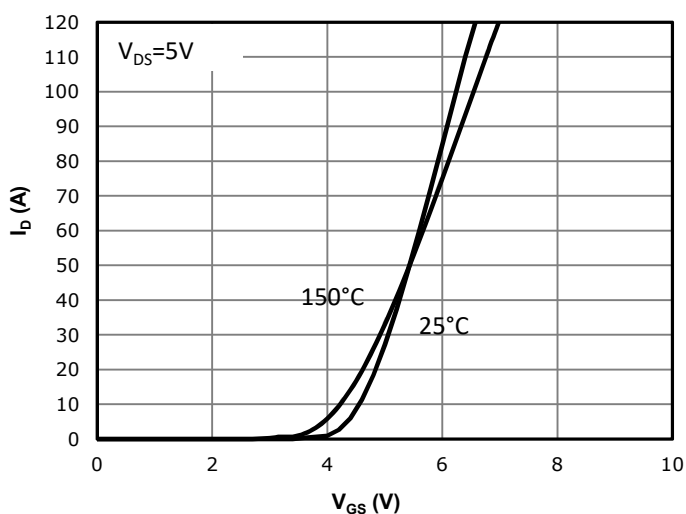


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

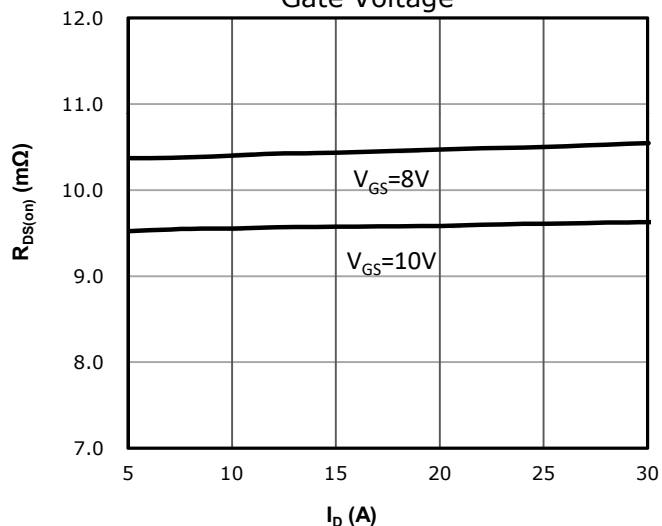


Fig 4: $R_{DS(on)}$ vs Gate Voltage

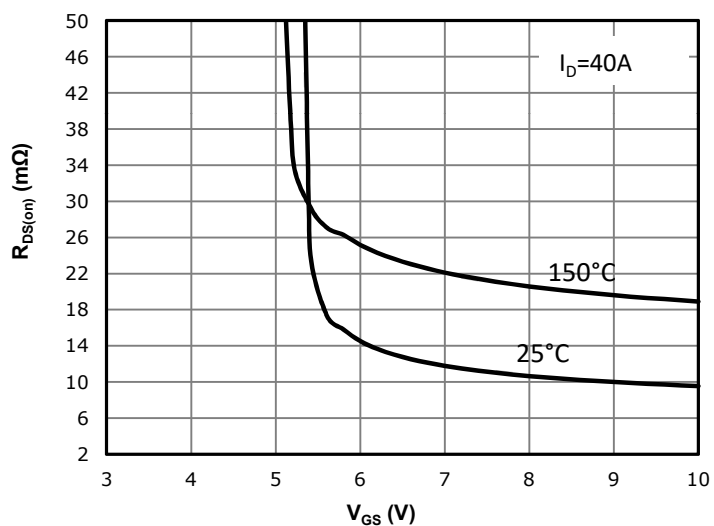


Fig 5: $R_{DS(on)}$ vs. Temperature

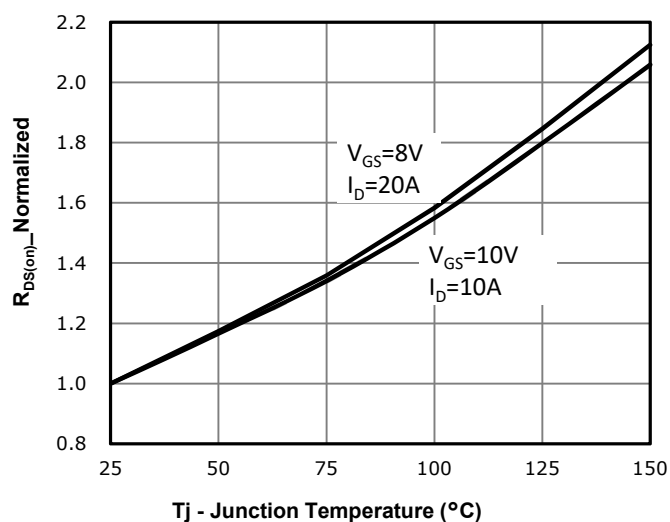


Fig 6: Capacitance Characteristics

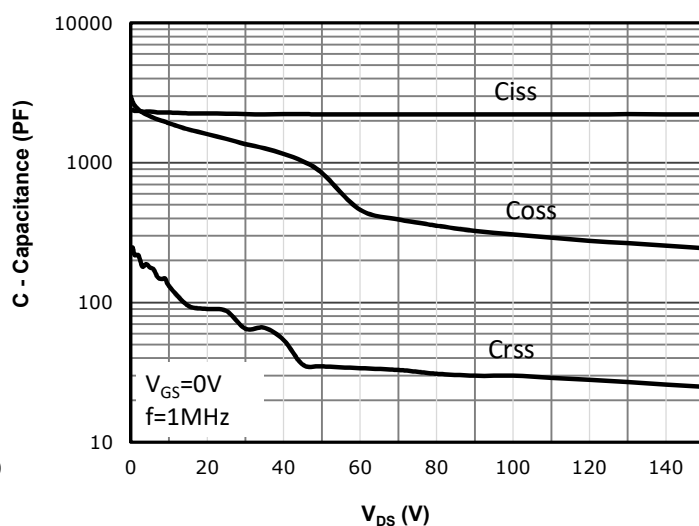


Fig 7: Gate Charge Characteristics

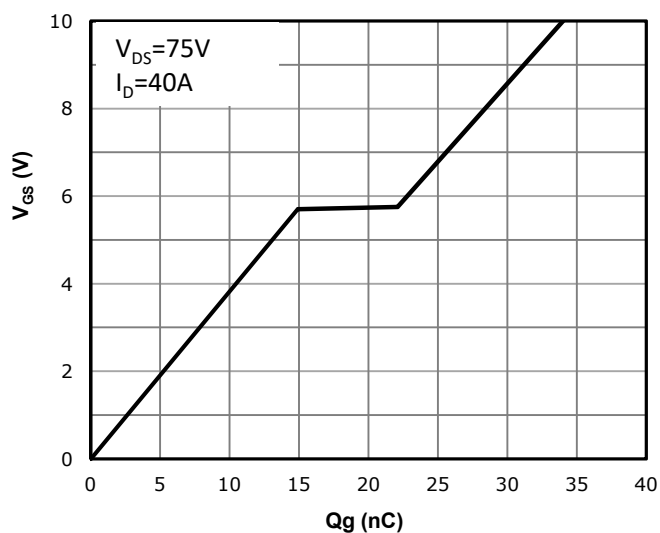


Fig 8: Body-diode Forward Characteristics

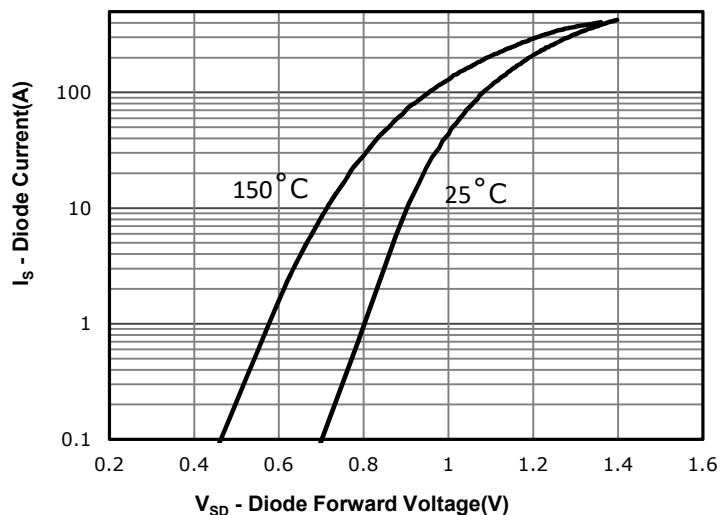


Fig 9: Power Dissipation

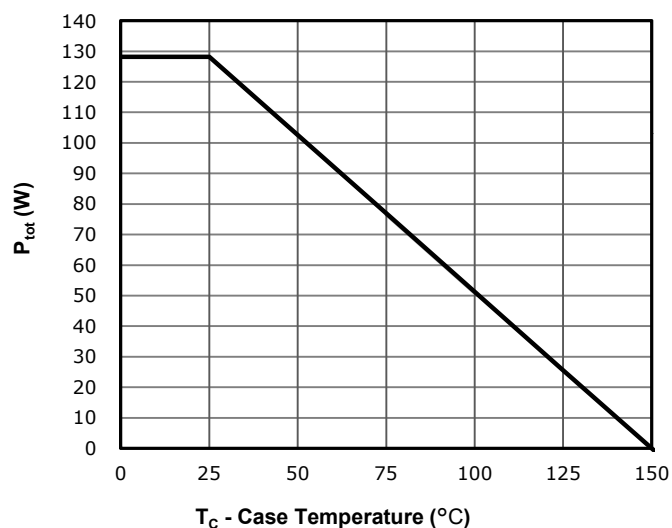


Fig 10: Drain Current Derating

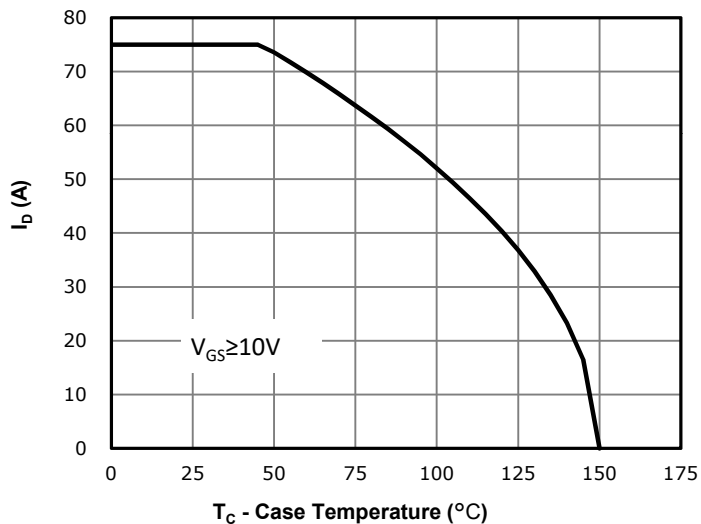


Fig 11: Safe Operating Area

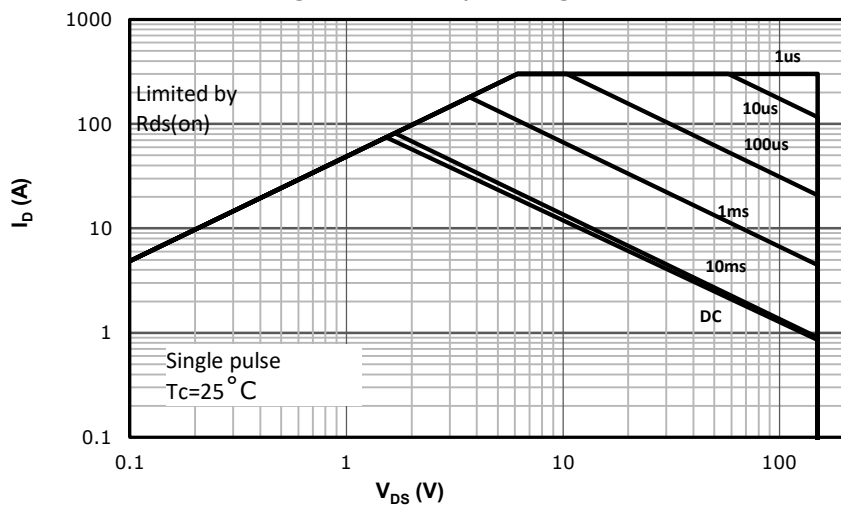
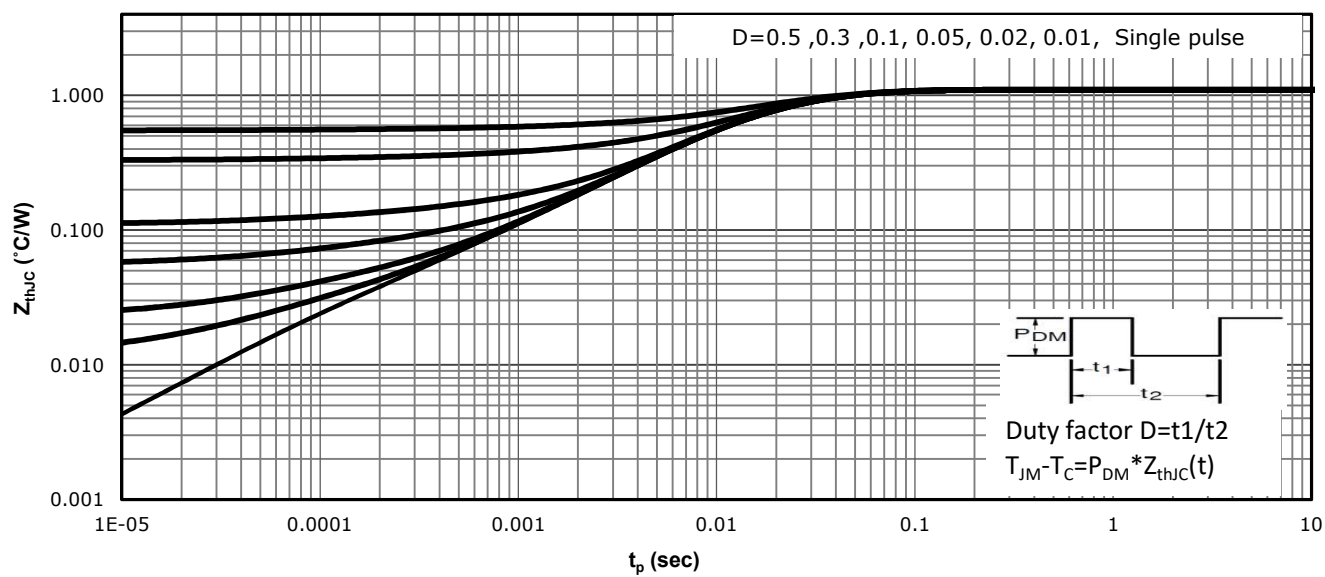
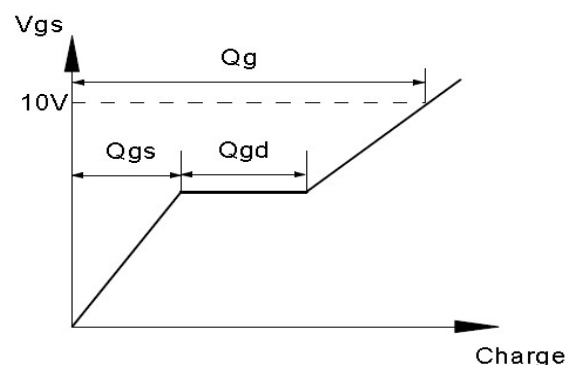
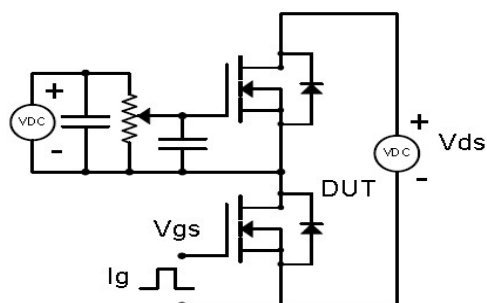


Fig 12: Max. Transient Thermal Impedance

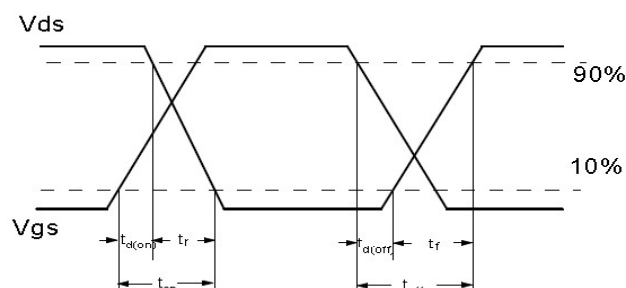
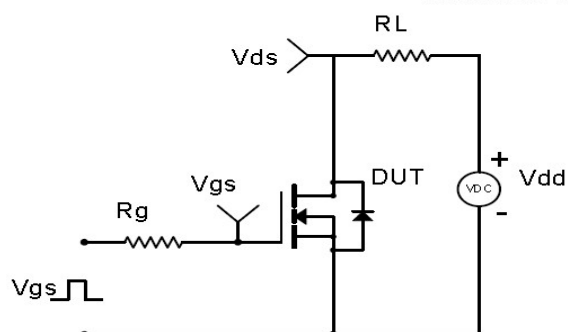


Test Circuit & Waveform

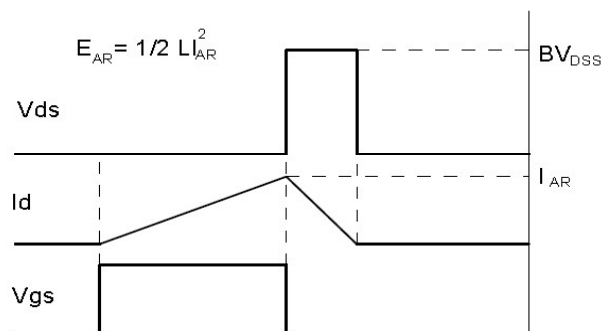
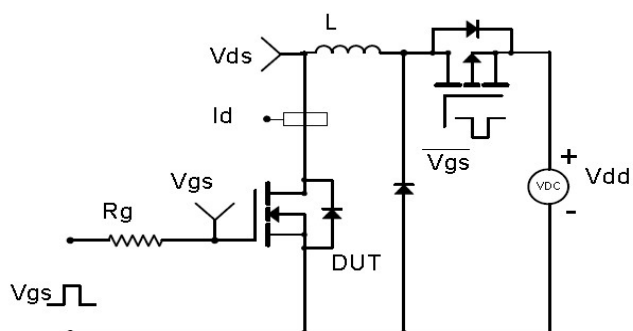
Gate Charge Test Circuit & Waveform



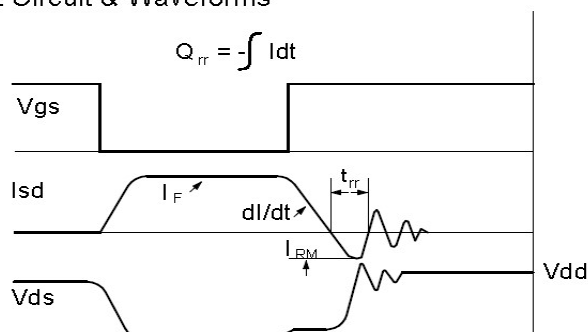
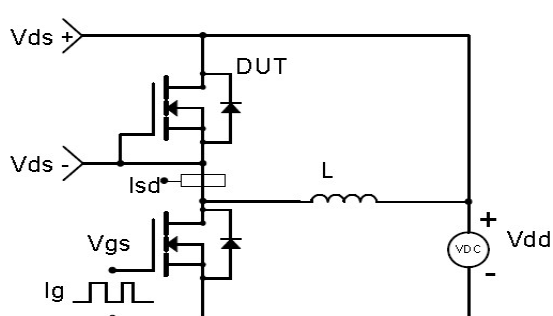
Resistive Switching Test Circuit & Waveforms



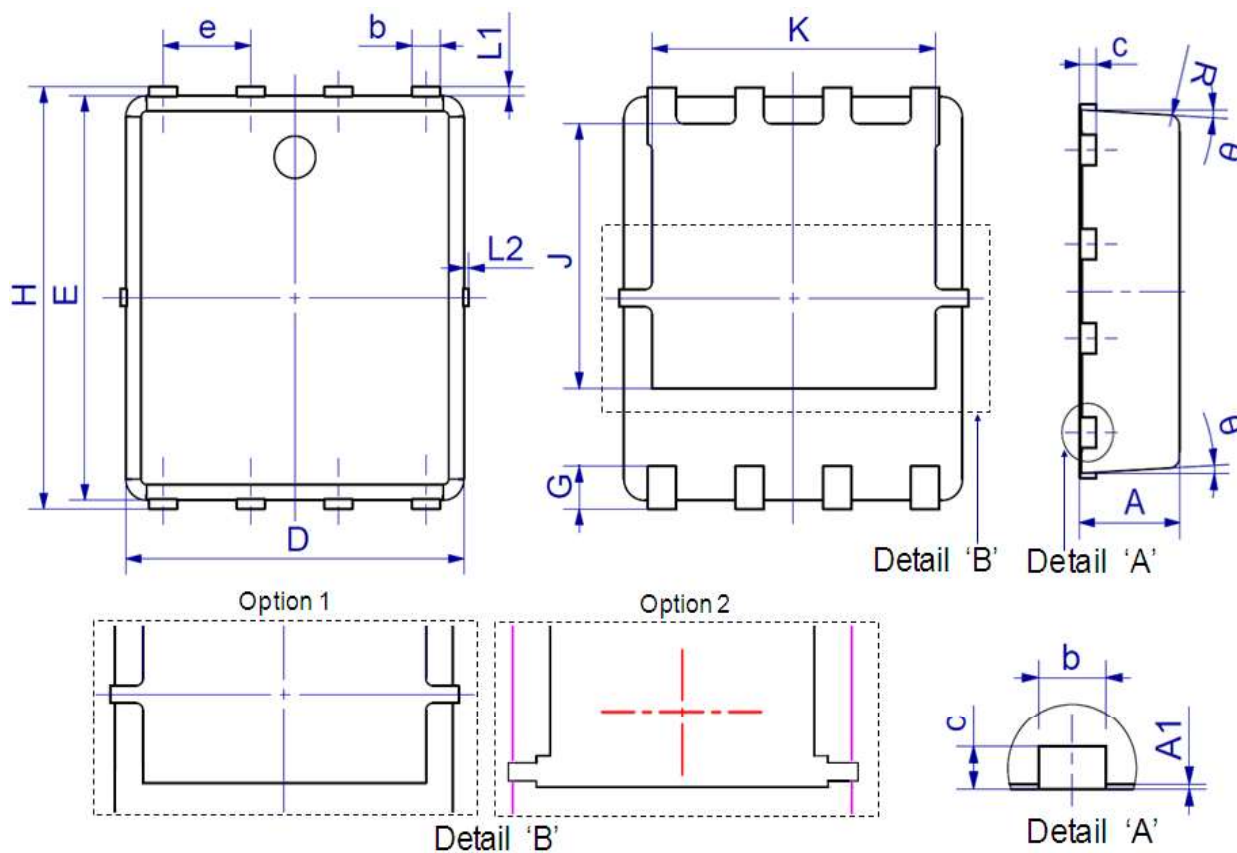
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: DFN5X6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.30	0.51	0.012	0.020
c	0.15	0.35	0.006	0.014
D	4.80	5.40	0.189	0.213
e	1.27 BSC		0.050 BSC	
E	5.66	6.06	0.223	0.239
G	0.30	0.71	0.012	0.028
H	5.90	6.35	0.232	0.250
J	3.32	3.92	0.131	0.154
K	3.61	4.25	0.142	0.167
L1	0.05	0.25	0.002	0.010
L2	0.00	0.15	0.000	0.006
R	0.25 REF		0.010 REF	
θ	0°	12°	0°	12°

Marking



NOTE:

NXBBAAAAY

N	—Wire Bond code
X	—Assembly location code
BB	—Fab code
AAAA	—Lot code
Y	—Bin code

Revision History

Revision	Date	Major changes
1.0	2022/11/9	Release of Preliminary Version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.